

Iodine Vacancy Redistribution in Organic–Inorganic Hybrid Perovskites: Light-Induced Switching Effects

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Wafer-scale reliable switching memory based on 2-dimensional layered organic–inorganic halide perovskite. <i>Nanoscale</i> , 2017, 9, 15278-15285.	5.6	113
2	Metal/Ion Interactions Induced p–n Junction in Methylammonium Lead Triiodide Perovskite Single Crystals. <i>Journal of the American Chemical Society</i> , 2017, 139, 17285-17288.	13.7	32
3	Competition between Metallic and Vacancy Defect Conductive Filaments in a $\text{CH}_3\text{NH}_3\text{PbI}_3$ -Based Memory Device. <i>Journal of Physical Chemistry C</i> , 2018, 122, 6431-6436.	3.1	115
4	Analytical Modeling of Organic–Inorganic $\text{CH}_3\text{NH}_3\text{PbI}_3$ Perovskite Resistive Switching and its Application for Neuromorphic Recognition. <i>Advanced Theory and Simulations</i> , 2018, 1, 1700035.	2.8	35
5	Coexistence of unipolar and bipolar resistive switching behaviors in NiFe_2O_4 thin film devices by doping Ag nanoparticles. <i>Journal of Applied Physics</i> , 2018, 123, .	2.5	28
6	Emerging perovskite materials for high density data storage and artificial synapses. <i>Journal of Materials Chemistry C</i> , 2018, 6, 1600-1617.	5.5	110
7	Optogenetics-Inspired Tunable Synaptic Functions in Memristors. <i>ACS Nano</i> , 2018, 12, 1242-1249.	14.6	205
8	Screening of point defects in methylammonium lead halides: a Monte Carlo study. <i>Journal of Materials Chemistry C</i> , 2018, 6, 1487-1494.	5.5	6
9	Light-current-induced acceleration of degradation of methylammonium lead iodide perovskite solar cells. <i>Journal of Power Sources</i> , 2018, 384, 303-311.	7.8	9
10	Lead-free, air-stable hybrid organic–inorganic perovskite resistive switching memory with ultrafast switching and multilevel data storage. <i>Nanoscale</i> , 2018, 10, 8578-8584.	5.6	136
11	Compliance-Free Multileveled Resistive Switching in a Transparent 2D Perovskite for Neuromorphic Computing. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 12768-12772.	8.0	64
12	From dead leaves to sustainable organic resistive switching memory. <i>Journal of Colloid and Interface Science</i> , 2018, 513, 774-778.	9.4	72
13	Effects of mobile charged defects on current–voltage behavior in resistive switching memories based on organic–inorganic hybrid perovskite. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	13
14	Multifunctional Optoelectronic Device Based on Resistive Switching Effects. , 0, , .		4
15	Intrinsic Behavior of $\text{CH}_3\text{NH}_3\text{PbBr}_3$ Single Crystals under Light Illumination. <i>Advanced Materials Interfaces</i> , 2018, 5, 1801206.	3.7	18
16	Control of Charge Recombination in Perovskites by Oxidation State of Halide Vacancy. <i>Journal of the American Chemical Society</i> , 2018, 140, 15753-15763.	13.7	129
17	Giant Zero-Drift Electronic Behaviors in Methylammonium Lead Halide Perovskite Diodes by Doping Iodine Ions. <i>Materials</i> , 2018, 11, 1606.	2.9	11
18	Synergies of Electrochemical Metallization and Valance Change in All–Inorganic Perovskite Quantum Dots for Resistive Switching. <i>Advanced Materials</i> , 2018, 30, e1800327.	21.0	246

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19	Biological Spiking Synapse Constructed from Solution Processed Bimetal Core–Shell Nanoparticle Based Composites. <i>Small</i> , 2018, 14, e1800288.	10.0	68
20	Phototunable Biomemory Based on Light–Mediated Charge Trap. <i>Advanced Science</i> , 2018, 5, 1800714.	11.2	99
21	Atomic Scale Photodetection Enabled by a Memristive Junction. <i>ACS Nano</i> , 2018, 12, 6706-6713.	14.6	37
22	Plasmon-Assisted Zone-Selective Repair of Nanoscale Electrical Breakdown Paths in Metal/Oxide/Metal Structures for Near-Field Optical Sensing. <i>ACS Applied Nano Materials</i> , 2018, 1, 4340-4350.	5.0	4
23	Light–Induced Anomalous Resistive Switches Based on Individual Organic–Inorganic Halide Perovskite Micro–Nanofibers. <i>Advanced Electronic Materials</i> , 2018, 4, 1800206.	5.1	26
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25	Influence of the voltage window on resistive switching memory characteristics based on g-C ₃ N ₄ device. <i>Ceramics International</i> , 2018, 44, 18108-18112.	4.8	15
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27	Phosphorene/ZnO Nano–Heterojunctions for Broadband Photonic Nonvolatile Memory Applications. <i>Advanced Materials</i> , 2018, 30, e1801232.	21.0	98
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